

ABSTRACTINSULATING FILM FOR SEMICONDUCTOR DEVICE AND
SEMICONDUCTOR DEVICE

To provide an insulating film having a low dielectric constant and performance sufficient as an interlayer insulating film of a semiconductor device, and a
5 semiconductor device using the insulating film.

An insulating film for a semiconductor device used as an interlayer insulating film of a semiconductor device, the insulating film consisting essentially of poly- α,α -difluoroparaxylylene and having a relative dielectric
10 constant of from 2.1 to 2.7. An insulating film for a semiconductor device used as an interlayer insulating film of a semiconductor device, the insulating film consisting essentially of poly- α,α -difluoroparaxylylene and exhibiting a step coverage of from 0.4 to 0.9. An
15 insulating film for a semiconductor device capable of being filled in a gap, the insulating film consisting essentially of poly- α,α -difluoroparaxylylene, having a ratio (D/L) of a depth (D) and an opening width (L) of 1 or more.

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